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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "<u>Embedded -</u> <u>Microcontrollers</u>"

Details

E·XFI

Product Status	Active
Core Processor	RL78
Core Size	16-Bit
Speed	32MHz
Connectivity	CSI, I ² C, IrDA, LINbus, UART/USART
Peripherals	LVD, POR, PWM, WDT
Number of I/O	44
Program Memory Size	32KB (32K x 8)
Program Memory Type	FLASH
EEPROM Size	4K x 8
RAM Size	5.5K x 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 5.5V
Data Converters	A/D 17x10b; D/A 1x8b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	48-LQFP
Supplier Device Package	48-LQFP (7x7)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f11bgcafb-30

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1.3.3 36-pin products

• 36-pin plastic WFLGA (4 × 4 mm, 0.5 mm pitch)



	A	В	С	D	E	F	
6	EVDD0	Vdd	P121/X1	P122/X2/EXCLK	P137/INTP0	P40/TOOL0	6
5	P61/SDAA0	P60/SCLA0	Vss	REGC	RESET	P124/XT2/ EXCLKS	5
4	P31/TI03/TO03/ INTP4/PCLBUZ0/ SSI00/(TRJIO0)/ VCOUT1	P14/ANI24/RxD2/ SI20/SDA20/ TRDIOD0/ (SCLA0)/IrRxD	P20/ANI0/ AVREFP/IVCMP12/ INTP11	P21/ANI1/ AVREFM/IVCMP13	P01/ANI16/TO00/ RxD1/TRGCLKB/ TRJIO0/INTP10/ IVCMP11	P123/XT1	4
3	P50/INTP1/SI00/ RxD0/TOOLRxD/ SDA00/TRGIOA/ (TRJO0)/ (TRDIOC1)	P70/INTP6/ (VCOUT0)/ (VCOUT1)	P15/PCLBUZ1/ SCK20/SCL20/ TRDIOB0/ (SDAA0)	P23/ANI3/ANO1/ PGAGND	P00/ANI17/TI00/ TxD1/TRGCLKA/ (TRJO0)/INTP8/ IVCMP10	P120/ANI19/ VCOUT0	3
2	P30/INTP3/ RTC1HZ/SCK00/ SCL00/TRJO0/ (TRDIOB1)	P16/TI01/TO01/ INTP5/TRDIOC0/ (RxD0)/ (TRDIOA1)	P12/ANI22/SO11/ TRDIOB1	P11/ANI21/SI11/ SDA11/TRDIOC1	P24/ANI4	P22/ANI2/ANO0/ PGAI/IVCMP0	2
1	P51/INTP2/SO00/ TxD0/TOOLTxD/ TRGIOB/ (TRDIOD1)	P17/TI02/TO02/ TRDIOA0/ TRDCLK0/(TxD0)/ (TRDIOD0)	P13/ANI23/TxD2/ SO20/TRDIOA1/ IrTxD	P10/ANI20/ SCK11/SCL11/ TRDIOD1/(TxD2)	P147/ANI18/ IVREF0	P25/ANI5	1
	Δ	B	C	П	F	F	

Caution 1. Connect the REGC pin to Vss pin via a capacitor (0.47 to 1 μ F).

Caution 2. Make VDD pin the potential that is higher than EVDD0 pin.

Remark 1. For pin identification, see 1.4 Pin Identification.

Remark 2. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection registers 0 to 3 (PIOR0 to PIOR3).

Remark 3. When using the microcontroller for an application where the noise generated inside the microcontroller must be reduced, it is recommended to supply separate powers to the VDD and EVDD0 pins.

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2.1 Absolute Maximum Ratings

Absolute Maximum Ratings

Deremeter	Cumbolo	Conditions	Datinga	Linit
Parameter	Symbols	Conduons	Raungs	Unit
Supply voltage	Vdd		-0.5 to +6.5	V
	EVDD0		-0.5 to +6.5	V
REGC pin input voltage	VIREGC	REGC	-0.3 to +2.8	V
			and -0.3 to VDD +0.3 Note 1	
Input voltage	VI1	P00 to P06, P10 to P17, P30, P31,	-0.3 to EVDD0 +0.3	V
		P40 to P43, P50 to P55, P70 to P77, P120,	and -0.3 to VDD +0.3 Note 2	
		P140, P141, P146, P147		
	VI2	P60 to P63 (N-ch open-drain)	-0.3 to +6.5	V
	Vi3	P20 to P27, P121 to P124, P137,	-0.3 to VDD +0.3 Note 2	V
		EXCLK, EXCLKS, RESET		
Output voltage	Vo1	P00 to P06, P10 to P17, P30, P31,	-0.3 to EVDD0 +0.3	V
		P40 to P43, P50 to P55, P60 to P63,	and -0.3 to VDD +0.3 Note 2	
		P70 to P77, P120, P130, P140, P141,		
		P146, P147		
	V02	P20 to P27	-0.3 to VDD +0.3 Note 2	V
Analog input voltage	VAI1	ANI16 to ANI24	-0.3 to EVDD0 +0.3	
			and -0.3 to AVREF(+) +0.3 Notes 2, 3	v
	VAI2	ANI0 to ANI7	-0.3 to VDD +0.3	V
			and -0.3 to AVREF(+) +0.3 Notes 2, 3	v

Note 1. Connect the REGC pin to Vss via a capacitor (0.47 to 1 μF). This value regulates the absolute maximum rating of the REGC pin. Do not use this pin with voltage applied to it.

Note 2. Must be 6.5 V or lower.

Note 3. Do not exceed AVREF (+) + 0.3 V in case of A/D conversion target pin.

- Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.
- Remark 1. Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.
- Remark 2. AVREF (+): + side reference voltage of the A/D converter.
- Remark 3. Vss: Reference voltage



Items	Symbol	Conditior	าร	MIN.	TYP.	MAX.	Unit
Output voltage, high	Voh1	P00 to P06, P10 to P17, P30, P31, P40 to P43, P50 to P55,	4.0 V ≤ EVDD0 ≤ 5.5 V, Іон1 = -10.0 mA	EVDD0 - 1.5			V
		P70 to P77, P120, P130, P140, P141, P146, P147	4.0 V ≤ EVDD0 ≤ 5.5 V, IOH1 = -3.0 mA	EVDD0 - 0.7			V
			2.7 V ≤ EVDD0 ≤ 5.5 V, Іон1 = -2.0 mA	EVDD0 - 0.6			V
			1.8 V ≤ EVDD0 ≤ 5.5 V, Іон1 = -1.5 mA	EVDD0 - 0.5			V
			1.6 V ≤ EVDD0 < 1.8 V, Іон1 = -1.0 mA	EVDD0 - 0.5			V
	Voh2	P20 to P27	1.6 V ≤ Vdd ≤ 5.5 V, Ioh2 = -100 μA	Vdd - 0.5			V
Output voltage, low	Vol1	P00 to P06, P10 to P17, P30, P31, P40 to P43, P50 to P55,	$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ IOL1 = 20.0 mA			1.3	V
		P70 to P77, P120, P130, P140, P141, P146, P147	$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ IOL1 = 8.5 mA			0.7	V
			$2.7 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ lol1 = 3.0 mA			0.6	V
			$2.7 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ lol1 = 1.5 mA			0.4	V
			$1.8 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ IOL1 = 0.6 mA			0.4	V
			$1.6 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ IOL1 = 0.3 mA			0.4	V
	Vol2	P20 to P27	$\begin{array}{l} 1.6 \text{ V} \leq \text{Vdd} \leq 5.5 \text{ V}, \\ \text{Iol2 = 400 } \mu\text{A} \end{array}$			0.4	V
	Vol3	P60 to P63	$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ IOL3 = 15.0 mA			2.0	V
			$4.0 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V},$ $\text{IOL3 = 5.0 \text{ mA}}$			0.4	V
			$2.7 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ lol3 = 3.0 mA			0.4	V
			$1.8 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V},$ $I_{\text{OL3}} = 2.0 \text{ mA}$			0.4	V
			$1.6 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V},$ IOL3 = 1.0 mA			0.4	V

(TA = -40 to +85°C, 1.6 V \leq EVDD0 \leq VDD \leq 5.5 V, VSS = EVSS0 = 0 V)

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Caution P00, P02 to P04, P10, P11, P13 to P15, P17, P30, P43, P50 to P55, P71, P74 do not output high level in N-ch opendrain mode.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

Parameter	Symbol			Conditions		MIN.	TYP.	MAX.	Unit
Supply current	IDD2	HALT mode	HS (high-speed main)	fносо = 64 MHz,	V _{DD} = 5.0 V		0.8	3.09	mA
Note 1	Note 2		mode Note 7	fiH = 32 MHz Note 4	VDD = 3.0 V		0.8	3.09	
				fносо = 32 MHz,	V _{DD} = 5.0 V		0.54	2.4	
				fiн = 32 MHz Note 4	V _{DD} = 3.0 V		0.54	2.4	
				fносо = 48 MHz,	V _{DD} = 5.0 V		0.62	2.4	
				fiн = 24 MHz Note 4	VDD = 3.0 V		0.62	2.4	
				fносо = 24 MHz,	V _{DD} = 5.0 V		0.44	1.83	
				fiн = 24 MHz Note 4	VDD = 3.0 V		0.44	1.83	
				fносо = 16 MHz,	VDD = 5.0 V		0.4	1.38	
				fiн = 16 MHz Note 4	VDD = 3.0 V		0.4	1.38	
			LS (low-speed main)	fносо = 8 MHz,	VDD = 3.0 V		260	790	μA
			mode Note 7	fiH = 8 MHz Note 4	VDD = 2.0 V		260	790	
			LV (low-voltage main)	fносо = 4 MHz,	V _{DD} = 3.0 V		420	830	μA
			mode Note 7	fiH = 4 MHz Note 4	VDD = 2.0 V		420	830	
			HS (high-speed main)	f _{MX} = 20 MHz ^{Note 3} ,	Square wave input		0.28	1.55	mA
			mode Note 7	VDD = 5.0 V	Resonator connection		0.49	1.74	
				f _{MX} = 20 MHz ^{Note 3} ,	Square wave input		0.28	1.55	
				VDD = 3.0 V	Resonator connection		0.49	1.74	
				f _{MX} = 10 MHz ^{Note 3} ,	Square wave input		0.19	0.86	
				VDD = 5.0 V	Resonator connection		0.3	0.93	
				f _{MX} = 10 MHz Note 3,	Square wave input		0.19	0.86	
				VDD = 3.0 V	Resonator connection		0.3	0.93	
			LS (low-speed main)	f _{MX} = 8 MHz ^{Note 3} ,	Square wave input		95	640	μA
			mode Note 7	VDD = 3.0 V	Resonator connection		145	680	
				f _{MX} = 8 MHz Note 3,	Square wave input		95	640	
				VDD = 2.0 V	Resonator connection		145	680	
			Subsystem clock	fsue = 32.768 kHz Note 5,	Square wave input		0.25	0.57	μA
			operation	TA = -40°C	Resonator connection		0.44	0.76	
				fsue = 32.768 kHz Note 5,	Square wave input		0.3	0.57	
				TA = 25°C	Resonator connection		0.49	0.76	
				fsue = 32.768 kHz Note 5,	Square wave input		0.36	1.17	
				TA = 50°C	Resonator connection		0.59	1.36	
				fsue = 32.768 kHz Note 5,	Square wave input		0.49	1.97	
				TA = 70°C	Resonator connection		0.72	2.16	
				fsue = 32.768 kHz Note 5,	Square wave input		0.97	3.37	
				TA = 85°C	Resonator connection		1.16	3.56	
	Idd3	STOP mode	TA = -40°C	·			0.18	0.51	μA
	Note 6	Note 8	T _A = +25°C				0.24	0.51	
			T _A = +50°C				0.29	1.1	
			T _A = +70°C				0.41	1.9	
			T _A = +85°C				0.9	3.3	

(TA = -40 to +85°C, 1.6 V \leq EVDD0 \leq VDD \leq 5.5 V, VSS = EVSS0 = 0 V)

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(Notes and Remarks are listed on the next page.)

2.4 AC Characteristics

Items	Symbol		Conditions		MIN.	TYP.	MAX.	Unit
Instruction cycle (min-	Тсү	Main system	HS (high-speed main)	$2.7~V \leq V_{DD} \leq 5.5~V$	0.03125		1	μs
imum instruction exe-		clock (fmain)	mode	$2.4 \text{ V} \leq \text{V}_{DD} < 2.7 \text{ V}$	0.0625		1	μs
cution time)		operation	LS (low-speed main) mode	$1.8 \text{ V} \leq \text{V}_{DD} \leq 5.5 \text{ V}$	0.125		1	μs
			LV (low-voltage main) mode	$1.6~V \le V_{DD} \le 5.5~V$	0.25		1	μs
		Subsystem clo	ock (fsuв) operation	$1.8~V \le V_{DD} \le 5.5~V$	28.5	30.5	31.3	μs
		In the self-	HS (high-speed main)	$2.7~V \leq V \text{DD} \leq 5.5~V$	0.03125		1	μs
		program-	mode	$2.4 \text{ V} \leq \text{V}_{DD} < 2.7 \text{ V}$	0.0625		1	μs
		ming mode	LS (low-speed main) mode	$1.8 \text{ V} \leq \text{V}_{DD} \leq 5.5 \text{ V}$	0.125		1	μs
			LV (low-voltage main) mode	$1.8 \text{ V} \leq \text{V}\text{DD} \leq 5.5 \text{ V}$	0.25		1	μs
External system clock	fEX	$2.7~V \leq V \text{DD} \leq$	5.5 V		1.0		20.0	MHz
frequency		$2.4~V \leq V \text{DD} \leq$	2.7 V		1.0		16.0	MHz
		$1.8 \text{ V} \le \text{V}_{\text{DD}}$ <	2.4 V		1.0		8.0	MHz
		$1.6 \text{ V} \le \text{V}_{\text{DD}}$ <	1.8 V		1.0		4.0	MHz
	fexs				32		35	kHz
External system clock	texн,	$2.7~V \leq V \text{DD} \leq$	5.5 V		24			ns
input high-level width,	texL	$2.4~V \leq V \text{DD} \leq$	2.7 V		30			ns
IOW-IEVEI WIQ[I]		$1.8 \text{ V} \le \text{V}_{\text{DD}}$ <	2.4 V		60			ns
		$1.6 V \le V_{DD} <$	1.8 V		120			ns
	texhs, texls				13.7			μs
TI00 to TI03 input high-level width, low- level width	ttiH, tti∟				1/fмск + 10 Note			ns
Timer RJ input cycle	fc	TRJIO		$2.7~V \leq EV_{DD0} \leq 5.5~V$	100			ns
				$1.8 \text{ V} \le \text{EV}_{\text{DD0}} < 2.7 \text{ V}$	300			ns
				$1.6 \text{ V} \leq \text{EV}_{\text{DD0}} < 1.8 \text{ V}$	500			ns
Timer RJ input high-	tтjiн,	TRJIO		$2.7~V \le EV \text{DD0} \le 5.5~V$	40			ns
level width, low-level	t⊤ji∟			$1.8 \text{ V} \le \text{EV}_{\text{DD0}} < 2.7 \text{ V}$	120			ns
				$1.6 \text{ V} \le \text{EV}_{\text{DD0}} < 1.8 \text{ V}$	200			ns

(TA = -40 to +85°C, 1.6 V \leq EVDD0 \leq VDD \leq 5.5 V, VSS = EVSS0 = 0 V)

NoteThe following conditions are required for low voltage interface when EVDD0 < VDD $1.8 V \le EVDD0 < 2.7 V$: MIN. 125 ns $1.6 V \le EVDD0 < 1.8 V$: MIN. 250 ns

Remark fmck: Timer array unit operation clock frequency (Operation clock to be set by the CKSmn bit of timer mode register mn (TMRmn). m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3))



(3) During communication at same potential (CSI mode) (master mode, SCKp... internal clock output) (TA = -40 to +85°C, 1.6 V \leq EVDD0 \leq VDD \leq 5.5 V, Vss = EVss0 = 0 V)

Parameter	Symbol	Conditions		HS (high-s main) mo	peed ode	LS (low-speed mode	d main)	LV (low-voltage main) mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	tKCY1	tkcy1 ≥ 4/fcLk	$2.7 \text{ V} \leq \text{Evddo} \leq 5.5 \text{ V}$	125		500		1000		ns
			$2.4 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V}$	250		500		1000		ns
			$1.8~V \le EV_{DD0} \le 5.5~V$	500		500		1000		ns
			$1.7 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}$	1000		1000		1000		ns
			$1.6~V \leq EV_{DD0} \leq 5.5~V$	—		1000		1000		ns
SCKp high-/low-level	tĸнı,	$4.0 \text{ V} \leq \text{EV}_{\text{DD0}}$	0 ≤ 5.5 V	tксү1/2 - 12		tксү1/2 - 50		tксү1/2 - 50		ns
width	tKL1	$2.7 \text{ V} \leq \text{EV}_{\text{DD0}}$	$\leq 5.5 V$	tксү1/2 - 18		tксү1/2 - 50		tксү1/2 - 50		ns
		$2.4 \text{ V} \leq \text{EV}_{\text{DD0}}$	$\leq 5.5 V$	tксү1/2 - 38		tксү1/2 - 50		tксү1/2 - 50		ns
		$1.8 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}$		tксү1/2 - 50		tксү1/2 - 50		tксү1/2 - 50		ns
		$1.7 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}$ t		tксү1/2 - 100		tксү1/2 - 100		tксү1/2 - 100		ns
		$1.6 \text{ V} \leq \text{EV}_{\text{DD0}}$	$\leq 5.5 V$	—		tксү1/2 - 100		tксү1/2 - 100		ns
SIp setup time	tsik1	$4.0 \text{ V} \leq \text{EV}_{\text{DD0}}$	$\leq 5.5 V$	44		110		110		ns
(to SCKp↑) Note 1		$2.7 \text{ V} \leq \text{EV}_{\text{DD0}}$	$1 \leq 5.5 \text{ V}$	44		110		110		ns
		$2.4 \text{ V} \leq \text{EV}_{\text{DD0}}$	$\leq 5.5 V$	75		110		110		ns
		$1.8 \text{ V} \leq \text{EV}_{\text{DD0}}$	$\leq 5.5 V$	110		110		110		ns
		$1.7 \text{ V} \leq \text{EV}_{\text{DD0}}$	$\leq 5.5 V$	220		220		220		ns
		$1.6 \text{ V} \leq \text{EV}_{\text{DD0}}$	$\leq 5.5 V$	—		220		220		ns
SIp hold time	tksi1	$1.7 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}$		19		19		19		ns
(from SCKp↑) Note 2		$1.6 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}$		—		19		19		ns
Delay time from SCKp↓ to SOp output	tkso1	$1.7 \text{ V} \le \text{EV}_{\text{DD0}}$ C = 30 pF Note	o ≤ 5.5 V e 4		25		25		25	ns
		$1.6 V \le EV_{DD0}$ C = 30 pF Note	o ≤ 5.5 V e 4		_		25		25	ns

Note 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 4. C is the load capacitance of the SCKp and SOp output lines.

Caution Select the normal input buffer for the SIp pin and the normal output mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

Remark 1. p: CSI number (p = 00, 01, 10, 11, 20, 21), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3), g: PIM number (g = 0, 1, 3, 5, 7)

Remark 2. fMck: Serial array unit operation clock frequency (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00 to 03, 10, 11))



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Parameter	Symbol	Conditions		HS (high-speed mode	d main)	LS (low-speed mode	main)	LV (low-voltage mode	e main)	Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SSI00 setup time	tssik	DAPmn = 0	$2.7 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}$	120		120		120		ns
			$1.8 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V}$	200		200		200		ns
			$1.7 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V}$	400		400		400		ns
			$1.6 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V}$	_		400		400		ns
		DAPmn = 1	$2.7 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V}$	1/fмск + 120		1/fмск + 120		1/fмск + 120		ns
			$1.8 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V}$	1/fмск + 200		1/fмск + 200		1/fмск + 200		ns
			$1.7 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V}$	1/fмск + 400		1/fмск + 400		1/fмск + 400		ns
			$1.6 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V}$	_		1/fмск + 400		1/fмск + 400		ns
SSI00 hold time	tĸssi	DAPmn = 0	$2.7 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V}$	1/fмск + 120		1/fмск + 120		1/fмск + 120		ns
			$1.8 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V}$	1/fмск + 200		1/fмск + 200		1/fмск + 200		ns
			$1.7 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}$	1/fмск + 400		1/fмск + 400		1/fмск + 400		ns
			$1.6 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V}$	_		1/fмск + 400		1/fмск + 400		ns
		DAPmn = 1	$2.7 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V}$	120		120		120		ns
			$1.8 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V}$	200		200		200		ns
			$1.7 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}$	400		400		400		ns
			$1.6 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}$	_		400		400		ns

(4) During communication at same potential (CSI mode) (slave mode, SCKp... external clock input) (TA = -40 to +85°C, 1.6 V \leq EVDD0 \leq VDD \leq 5.5 V, VSs = EVSs0 = 0 V)

Caution Select the normal input buffer for the SIp pin and SCKp pin and the normal output mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

Remark p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0), g: PIM number (g = 3, 5)

CSI mode connection diagram (during communication at same potential)



CSI mode connection diagram (during communication at same potential) (Slave Transmission of slave select input function (CSI00))



Remark 1. p: CSI number (p = 00, 01, 10, 11, 20, 21) **Remark 2.** m: Unit number, n: Channel number (mn = 00 to 03, 10, 11)



(7) Communication at different potential (2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output, corresponding CSI00 only)

Parameter	Symbol	Conditions	Conditions HS (high-speed ma mode		LS (low-speed main) mode		LV (low-voltage main) mode		Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SIp setup time (to SCKp↓) ^{Note 2}	tsıĸı		23		110		110		ns
		$\label{eq:2.7} \begin{split} & 2.7 \; V \leq EV_{DD0} < 4.0 \; V, \\ & 2.3 \; V \leq V_b \leq 2.7 \; V, \\ & C_b = 20 \; pF, \; R_b = 2.7 \; k\Omega \end{split}$	33		110		110		ns
SIp hold time (from SCKp↓) ^{Note 2}	tĸsıı	$\begin{array}{l} 4.0 \; V \leq EV_{DD0} \leq 5.5 \; V, \\ 2.7 \; V \leq V_b \leq 4.0 \; V, \\ C_b = 20 \; pF, \; R_b = 1.4 \; k\Omega \end{array}$	10		10		10		ns
		$\label{eq:2.7} \begin{array}{l} 2.7 \; V \leq EV_{DD0} < 4.0 \; V, \\ 2.3 \; V \leq V_b \leq 2.7 \; V, \\ C_b = 20 \; pF, \; R_b = 2.7 \; k\Omega \end{array}$	10		10		10		ns
Delay time from SCKp↑ to SOp output ^{Note 2}	tkso1	$\begin{array}{l} 4.0 \; V \leq EV_{DD0} \leq 5.5 \; V, \\ 2.7 \; V \leq V_b \leq 4.0 \; V, \\ C_b = 20 \; pF, \; R_b = 1.4 \; k\Omega \end{array}$		10		10		10	ns
		$\label{eq:2.7} \begin{split} & 2.7 \; V \leq EV_{DD0} < 4.0 \; V, \\ & 2.3 \; V \leq V_b \leq 2.7 \; V, \\ & C_b = 20 \; pF, \; R_b = 2.7 \; k\Omega \end{split}$		10		10		10	ns

(TA = -40 to +85°C, 2.7 V \leq EVDD0 \leq VDD \leq 5.5 V, VSS = EVSS0 = 0 V)

(2/2)

Note 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.

Note 2. When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (VDD tolerance (for the 48-, 32-, 24-pin products)/EVDD tolerance (for the 64-, 36-pin products)) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

Remark 1. Rb[Ω]: Communication line (SCKp, SOp) pull-up resistance, Cb[F]: Communication line (SCKp, SOp) load capacitance, Vb[V]: Communication line voltage

Remark 2. p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0), g: PIM and POM number (g = 3, 5)

Remark 3. fmck: Serial array unit operation clock frequency (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number

Remark 4. This value is valid only when CSI00's peripheral I/O redirect function is not used.

(mn = 00))



.....

(10) Communication at different potential (1.8 V, 2.5 V, 3 V) (simplified I²C mode)

(1A = -40 to +8)	5°C, 1.8	$V \leq EVDD0 \leq VDD \leq 5.$	5 V, VSS = EVSS	50 = U	v)				(2/2)
Parameter	Symbol	Conditions	HS (high-speed r mode	nain)	LS (low-speed m mode	nain)	LV (low-voltage r mode	nain)	Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Data setup time (reception)	tsu:dat	$\begin{array}{l} 4.0 \; V \leq EV_{DD0} \leq 5.5 \; V, \\ 2.7 \; V \leq V_b \leq 4.0 \; V, \\ C_b = 50 \; pF, \; R_b = 2.7 \; k\Omega \end{array}$	1/fмск + 135 Note 3		1/f _{MCK} + 190 Note 3		1/fмск + 190 Note 3		ns
		$\label{eq:2.7} \begin{array}{l} 2.7 \ V \leq EV_{DD0} < 4.0 \ V, \\ 2.3 \ V \leq V_b \leq 2.7 \ V, \\ C_b = 50 \ pF, \ R_b = 2.7 \ k\Omega \end{array}$	1/fмск + 135 Note 3		1/f _{MCK} + 190 Note 3		1/fmck + 190 Note 3		ns
			1/fмск + 190 Note 3		1/fмск + 190 Note 3		1/fмск + 190 Note 3		ns
		$\label{eq:2.7} \begin{array}{l} 2.7 \ V \leq EV_{DD0} < 4.0 \ V, \\ 2.3 \ V \leq V_b \leq 2.7 \ V, \\ C_b = 100 \ pF, \ R_b = 2.7 \ k\Omega \end{array}$	1/fмск + 190 Note 3		1/fмск + 190 Note 3		1/fмск + 190 Note 3		ns
		$ \begin{split} & 1.8 \ \text{V} \leq \text{EV}_{\text{DD0}} < 3.3 \ \text{V}, \\ & 1.6 \ \text{V} \leq \text{V}_{b} \leq 2.0 \ \text{V}^{\ \text{Note 2}}, \\ & \text{C}_{b} = 100 \ \text{pF}, \ \text{R}_{b} = 5.5 \ \text{k}\Omega \end{split} $	1/fмск + 190 Note 3		1/fмск + 190 Note 3		1/fмск + 190 Note 3		ns
Data hold time (transmission)	thd:dat	$\begin{array}{l} 4.0 \; V \leq EV_{DD0} \leq 5.5 \; V, \\ 2.7 \; V \leq V_b \leq 4.0 \; V, \\ C_b = 50 \; pF, \; R_b = 2.7 \; k\Omega \end{array}$	0	305	0	305	0	305	ns
		$\begin{array}{l} 2.7 \ V \leq EV_{DD0} < 4.0 \ V, \\ 2.3 \ V \leq V_b \leq 2.7 \ V, \\ C_b = 50 \ pF, \ R_b = 2.7 \ k\Omega \end{array}$	0	305	0	305	0	305	ns
			0	355	0	355	0	355	ns
		$\begin{array}{l} 2.7 \ V \leq EV_{DD0} < 4.0 \ V, \\ 2.3 \ V \leq V_b \leq 2.7 \ V, \\ C_b = 100 \ pF, \ R_b = 2.7 \ k\Omega \end{array}$	0	355	0	355	0	355	ns
			0	405	0	405	0	405	ns

< \/p 55V V

The value must also be equal to or less than fMCK/4. Note 1.

Note 2. Use it with $EVDD0 \ge Vb$.

Set the fMCK value to keep the hold time of SCLr = "L" and SCLr = "H". Note 3.

Caution Select the TTL input buffer and the N-ch open drain output (VDD tolerance (for the 48-, 32-, 24-pin products)/EVDD tolerance (for the 64-, 36-pin products)) mode for the SDAr pin and the N-ch open drain output (VDD tolerance (for the 48-, 32-, 24-pin products)/EVDD tolerance (for the 64-, 36-pin products)) mode for the SCLr pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

(Remarks are listed on the next page.)



Items	Symbol	Conditi	ons	MIN.	TYP.	MAX.	Unit	
Input leakage cur- rent, high	put leakage cur- int, high ILIH1 P00 to P06, P10 to P17, P30, P31, P40 to P43, P50 to P55, P70 to P77, P120, P140, P141, P146, P147		VI = EVDDO)			1	μA
	ILIH2	P20 to P27, P137, RESET	VI = VDD				1	μA
	ILIH3	P121 to P124 (X1, X2, EXCLK, XT1, XT2, EXCLKS)	VI = VDD	In input port or external clock input			1	μA
				In resonator con- nection			10	μA
Input leakage current, low	ILIL1	P00 to P06, P10 to P17, P30, P31, P40 to P43, P50 to P55, P70 to P77, P120, P140, P141, P146, P147	VI = EVsso				-1	μA
	ILIL2	P20 to P27, P137, RESET	VI = VSS				-1	μA
	ILIL3	P121 to P124 (X1, X2, EXCLK, XT1, XT2, EXCLKS)	VI = VSS	In input port or external clock input			-1	μA
				In resonator con- nection			-10	μA
On-chip pull-up resistance	Ru	P00 to P06, P10 to P17, P30, P31, P40 to P43, P50 to P55, P70 to P77, P120, P140, P141, P146, P147	VI = EVsso	, In input port	10	20	100	kΩ

($(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{DI}$	$00 \le VDD \le 5.5 V. VSS = EVSS0 = 0 V.$
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Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.



•		•		,					• •
Parameter	Symbol			Conditions		MIN.	TYP.	MAX.	Unit
Supply current	IDD2	HALT mode	HS (high-speed main)	fносо = 64 MHz,	V _{DD} = 5.0 V		0.80	4.36	mA
Note 1	Note 2		mode Note 7	fiH = 32 MHz Note 4	V _{DD} = 3.0 V		0.80	4.36	
				fносо = 32 MHz,	V _{DD} = 5.0 V		0.54	3.67	
				fiн = 32 MHz Note 4	V _{DD} = 3.0 V		0.54	3.67	
				fносо = 48 MHz,	V _{DD} = 5.0 V		0.62	3.42	
				fin = 24 MHz Note 4	V _{DD} = 3.0 V		0.62	3.42	
				fносо = 24 MHz,	V _{DD} = 5.0 V		0.44	2.85	
				fiH = 24 MHz Note 4	V _{DD} = 3.0 V		0.44	2.85	
				fносо = 16 MHz,	V _{DD} = 5.0 V		0.40	2.08	
				fiH = 16 MHz Note 4	V _{DD} = 3.0 V		0.40	2.08	
			HS (high-speed main) mode ^{Note 7}	fmx = 20 MHz Note 3, VDD = 5.0 V fmx = 20 MHz Note 3, VDD = 3.0 V	Square wave input		0.28	2.45	mA
					Resonator connection		0.49	2.57	
					Square wave input		0.28	2.45	-
					Resonator connection		0.49	2.57	
				f _{MX} = 10 MHz ^{Note 3} , V _{DD} = 5.0 V	Square wave input		0.19	1.28	
					Resonator connection		0.30	1.36	
				f _{MX} = 10 MHz ^{Note 3} , V _{DD} = 3.0 V	Square wave input		0.19	1.28	
					Resonator connection		0.30	1.36	
			Subsystem clock operation	$f_{SUB} = 32.768 \text{ kHz Note 5},$ $T_A = -40^{\circ}\text{C}$ $f_{SUB} = 32.768 \text{ kHz Note 5},$ $T_A = +25^{\circ}\text{C}$ $f_{SUB} = 32.768 \text{ kHz Note 5},$	Square wave input		0.25	0.57	μΑ
					Resonator connection		0.44	0.76	
					Square wave input		0.30	0.57	
					Resonator connection		0.49	0.76	
					Square wave input		0.36	1.17	
				TA = +50°C fsub = 32.768 kHz ^{Note 5} , TA = +70°C	Resonator connection		0.59	1.36	
					Square wave input		0.49	1.97	1
					Resonator connection		0.72	2.16	
				fsue = 32.768 kHz Note 5,	Square wave input		0.97	3.37	
				TA = +85°C	Resonator connection		1.16	3.56	
				fsue = 32.768 kHz Note 5,	Square wave input		3.20	17.10]
				TA = +105°C	Resonator connection		3.40	17.50	
	IDD3	STOP mode	TA = -40°C				0.18	0.51	μΑ
	Note 6	te 6 Note 8	$T_{A} = +25^{\circ}C$ $T_{A} = +50^{\circ}C$				0.24	0.51	
							0.29	1.10	
			TA = +70°C				0.41	1.90	
			TA = +85°C				0.90	3.30	
			TA = +105°C				3.10	17.00	1

(TA = -40 to +105°C, 2.4 V \leq EVDD0 \leq VDD \leq 5.5 V, Vss = EVsso = 0 V)

(2/2)

(Notes and Remarks are listed on the next page.)

Parameter	Symbol	Conditi	ions	MIN.	TYP.	MAX.	Unit
Low-speed on-chip oscilla- tor operating current	I _{FIL} Note 1				0.2		μA
RTC operating current	IRTC Notes 1, 2, 3				0.02		μΑ
12-bit interval timer operat- ing current	IIT Notes 1, 2, 4				0.02		μA
Watchdog timer operating current	IWDT Notes 1, 2, 5	fı∟ = 15 kHz			0.22		μA
A/D converter operating cur- rent	I _{ADC} Notes 1, 6	When conversion at maximum speed	Normal mode, AV _{REFP} = V _{DD} = 5.0 V		1.3	1.7	mA
			Low voltage mode, AV _{REFP} = V _{DD} = 3.0 V		0.5	0.7	mA
A/D converter reference voltage current	IADREF Note 1				75		μA
Temperature sensor operat- ing current	ITMPS Note 1				75		μA
D/A converter operating cur- rent	IDAC Notes 1, 11	Per D/A converter channel				1.5	mA
PGA operating current		Operation			480	700	μΑ
Comparator operating cur- rent	ICMP Notes 1, 12	Operation (per comparator chan- nel, constant current for compara-	When the internal reference voltage is not in use		50	100	μΑ
		tor included)	When the internal reference voltage is in use		60	110	μΑ
LVD operating current	ILVD Notes 1, 7				0.08		μA
Self-programming operat- ing current	IFSP Notes 1, 9				2.50	12.2	mA
BGO operating current	IBGO Notes 1, 8				2.50	12.2	mA
SNOOZE operating current	I _{SNOZ} Note 1	ADC operation	The mode is performed Note 10		0.50	1.10	mA
			The A/D conversion opera- tions are performed, Low volt- age mode, AV _{REFP} = V _{DD} = 3.0 V		1.20	2.04	
		CSI/UART operation			0.70	1.54	
		DTC operation			3.10		

Note 1. Current flowing to VDD.

Note 2. When high speed on-chip oscillator and high-speed system clock are stopped.

- Note 3. Current flowing only to the real-time clock (RTC) (excluding the operating current of the low-speed on-chip oscillator and the XT1 oscillator). The supply current of the RL78 microcontrollers is the sum of the values of either IDD1 or IDD2, and IRTC, when the real-time clock operates in operation mode or HALT mode. When the low-speed on-chip oscillator is selected, IFIL should be added. IDD2 subsystem clock operation includes the operational current of the real-time clock.
- Note 4. Current flowing only to the 12-bit interval timer (excluding the operating current of the low-speed on-chip oscillator and the XT1 oscillator). The supply current of the RL78 microcontrollers is the sum of the values of either IDD1 or IDD2, and IIT, when the 12-bit interval timer operates in operation mode or HALT mode. When the low-speed on-chip oscillator is selected, IFIL should be added.
- Note 5. Current flowing only to the watchdog timer (including the operating current of the low-speed on-chip oscillator). The supply current of the RL78 microcontrollers is the sum of IDD1, IDD2 or IDD3 and IWDT when the watchdog timer is in operation.
- **Note 6.** Current flowing only to the A/D converter. The supply current of the RL78 microcontrollers is the sum of IDD1 or IDD2 and IADC when the A/D converter operates in an operation mode or the HALT mode.
- Note 7. Current flowing only to the LVD circuit. The supply current of the RL78 microcontrollers is the sum of IDD1, IDD2 or IDD3 and ILVD when the LVD circuit is in operation.
- **Note 8.** Current flowing during programming of the data flash.
- **Note 9.** Current flowing during self-programming.
- Note 10. For shift time to the SNOOZE mode, see 26.3.3 SNOOZE mode in the RL78/G1F User's Manual.

3.4 AC Characteristics

Items	Symbol		Conditions		MIN.	TYP.	MAX.	Unit
Instruction cycle (min-	Тсү	Main system clock (fMAIN) operation	HS (high-speed main)	$2.7~V \leq V_{DD} \leq 5.5~V$	0.03125		1	μs
imum instruction exe- cution time)			mode	$2.4 \text{ V} \leq \text{V}_{\text{DD}} < 2.7 \text{ V}$	0.0625		1	μs
		Subsystem clock (fsub) operation		$2.4~\text{V} \leq \text{V}\text{DD} \leq 5.5~\text{V}$	28.5	30.5	31.3	μs
		In the self-	HS (high-speed main)	$2.7~V \le V_{DD} \le 5.5~V$	0.03125		1	μs
		program- mode ming mode	mode	$2.4 \text{ V} \leq \text{V}_{\text{DD}} < 2.7 \text{ V}$	0.0625		1	μs
External system clock	fEX	$2.7~V \leq V \text{DD} \leq$	5.5 V		1.0		20.0	MHz
frequency		$2.4 \text{ V} \leq \text{Vdd} \leq 2.7 \text{ V}$			1.0		16.0	MHz
	fexs				32		35	kHz
External system clock	texн,	$2.7~V \leq V_{DD} \leq$	5.5 V		24			ns
input high-level width,	texL	$2.4~V \leq V_{DD} \leq$	2.7 V		30			ns
low-level width	texhs, texls				13.7			μs
TI00 to TI03 input high-level width, low- level width	ttiH, tti∟				1/fмск + 10 Note			ns
Timer RJ input cycle	fc	TRJIO		$2.7 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}$	100			ns
				$2.4 \text{ V} \le \text{EV}_{\text{DD0}} \le 2.7 \text{ V}$	300			ns
Timer RJ input high-	tтjiн,	TRJIO		$2.7 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}$	40			ns
level width, low-level width	t⊤ji∟			$2.4 \text{ V} \le \text{EV}_{\text{DD0}} < 2.7 \text{ V}$	120			ns

(TA = -40 to +105°C, 2.4 V \leq EVDD0 \leq VDD \leq 5.5 V, VSS = EVSS0 = 0 V)

Note The following conditions are required for low voltage interface when EVDD0 < VDD

2.4 V ≤ EVDD0 < 2.7 V: MIN. 125 ns

Remark fMCK: Timer array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of timer mode register mn (TMRmn). m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3))



Minimum Instruction Execution Time during Main System Clock Operation

TCY vs VDD (HS (high-speed main) mode)



Supply voltage VDD [V]





CSI mode serial transfer timing (during communication at same potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)

CSI mode serial transfer timing (during communication at same potential) (When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



Remark 1. p: CSI number (p = 00, 01, 10, 11, 20, 21) Remark 2. m: Unit number, n: Channel number (mn = 00 to 03, 10, 11)

Note 5. The smaller maximum transfer rate derived by using fMCK/6 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 2.4 V \leq EVDD0 < 3.3 V and 1.6 V \leq Vb \leq 2.0 V

Maximum transfer rate =
$$\frac{1}{\{-C_b \times R_b \times \ln (1 - \frac{1.5}{V_b})\} \times 3}$$
Baud rate error (theoretical value) =
$$\frac{\frac{1}{|\text{Transfer rate} \times 2|} - \{-C_b \times R_b \times \ln (1 - \frac{1.5}{V_b})\}}{(\frac{1}{|\text{Transfer rate}|}) \times \text{Number of transferred bits}} \times 100 [\%]$$

* This value is the theoretical value of the relative difference between the transmission and reception sides.

- Note 6.This value as an example is calculated when the conditions described in the "Conditions" column are met.Refer to Note 5 above to calculate the maximum transfer rate under conditions of the customer.
- Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (VDD tolerance (for the 48-, 32-, 24pin products)/EVDD tolerance (for the 64-, 36-pin products)) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

(Remarks are listed on the next page.)



(8) Communication at different potential (1.8 V, 2.5 V, 3 V) (simplified I²C mode)

(TA = -40 to +105°C, 2.4 V \leq EVDD0 \leq VDD \leq 5.5 V, VSS = EVSS0 = 0 V)

(1/2)

Parameter	Symbol	Conditions	HS (high-spe	ed main) mode	Unit
			MIN.	MAX.	
SCLr clock frequency	fsc∟	$\begin{array}{l} 4.0 \; V \leq EV_{DD0} \leq 5.5 \; V, \\ 2.7 \; V \leq V_b \leq 4.0 \; V, \\ C_b = 50 \; pF, \; R_b = 2.7 \; k\Omega \end{array}$		400 Note 1	kHz
		$\label{eq:2.7} \begin{array}{l} 2.7 \; V \leq EV_{DD0} < 4.0 \; V, \\ 2.3 \; V \leq V_b \leq 2.7 \; V, \\ C_b = 50 \; pF, \; R_b = 2.7 \; k\Omega \end{array}$		400 Note 1	kHz
				100 Note 1	kHz
		$\label{eq:2.7} \begin{array}{l} 2.7 \; V \leq EV_{DD0} < 4.0 \; V, \\ 2.3 \; V \leq V_b \leq 2.7 \; V, \\ C_b = 100 \; pF, \; R_b = 2.7 \; k\Omega \end{array}$		100 Note 1	kHz
		$\label{eq:2.4} \begin{array}{l} 2.4 \ V \leq EV_{DD0} < 3.3 \ V, \\ 1.6 \ V \leq V_b \leq 2.0 \ V, \\ C_b = 100 \ p\text{F}, \ R_b = 5.5 \ k\Omega \end{array}$		100 Note 1	kHz
Hold time when SCLr = "L"	tLOW	$\begin{array}{l} 4.0 \; V \leq EV_{DD0} \leq 5.5 \; V, \\ 2.7 \; V \leq V_b \leq 4.0 \; V, \\ C_b = 50 \; pF, \; R_b = 2.7 \; k\Omega \end{array}$	1200		ns
		$\label{eq:2.7} \begin{array}{l} 2.7 \; V \leq EV_{DD0} < 4.0 \; V, \\ 2.3 \; V \leq V_b \leq 2.7 \; V, \\ C_b = 50 \; pF, \; R_b = 2.7 \; k\Omega \end{array}$	1200		ns
			4600	ns	
	$\begin{array}{c} 2.7 \ V \leq EV_{DD0} < 4.0 \\ 2.3 \ V \leq V_b \leq 2.7 \ V, \\ C_b = 100 \ pF, \ R_b = 2. \\ \hline 2.4 \ V \leq EV_{DD0} < 3.3 \\ 1.6 \ V \leq V_b \leq 2.0 \ V, \\ C_b = 100 \ pF, \ R_b = 5. \end{array}$	$\label{eq:2.7} \begin{array}{l} 2.7 \; V \leq EV_{DD0} < 4.0 \; V, \\ 2.3 \; V \leq V_b \leq 2.7 \; V, \\ C_b = 100 \; pF, \; R_b = 2.7 \; k\Omega \end{array}$	4600		ns
		$\label{eq:2.4} \begin{array}{l} 2.4 \ V \leq EV_{DD0} < 3.3 \ V, \\ 1.6 \ V \leq V_b \leq 2.0 \ V, \\ C_b = 100 \ p\text{F}, \ R_b = 5.5 \ k\Omega \end{array}$	4650		ns
Hold time when SCLr = "H"	tнıgн	$\begin{array}{l} 4.0 \; V \leq EV_{DD0} \leq 5.5 \; V, \\ 2.7 \; V \leq V_{b} \leq 4.0 \; V, \\ C_{b} = 50 \; pF, \; R_{b} = 2.7 \; k\Omega \end{array}$	620		ns
	$\begin{array}{l} 2.7 \; V \leq EV_{DD0} < 4.0 \\ 2.3 \; V \leq V_b \leq 2.7 \; V, \\ C_b = 50 \; pF, \; R_b = 2.7 \end{array}$	$\label{eq:2.7} \begin{array}{l} 2.7 \; V \leq EV_{DD0} < 4.0 \; V, \\ 2.3 \; V \leq V_b \leq 2.7 \; V, \\ C_b = 50 \; pF, \; R_b = 2.7 \; k\Omega \end{array}$	500		ns
		$\begin{array}{l} 4.0 \; V \leq EV_{DD0} \leq 5.5 \; V, \\ 2.7 \; V \leq V_{b} \leq 4.0 \; V, \\ C_{b} = 100 \; pF, \; R_{b} = 2.8 \; k\Omega \end{array}$	2700		ns
		$\label{eq:2.7} \begin{array}{l} 2.7 \; V \leq EV_{DD0} < 4.0 \; V, \\ 2.3 \; V \leq V_b \leq 2.7 \; V, \\ C_b = 100 \; pF, \; R_b = 2.7 \; k\Omega \end{array}$	2400		ns
		$\label{eq:Vb} \begin{array}{l} 2.4 \ V \leq EV_{DD0} < 3.3 \ V, \\ 1.6 \ V \leq V_b \leq 2.0 \ V, \\ C_b = 100 \ p\text{F}, \ R_b = 5.5 \ k\Omega \end{array}$	1830		ns



(4) When reference voltage (+) = Internal reference voltage (ADREFP1 = 1, ADREFP0 = 0), reference voltage (-) = AVREFM/ANI1 (ADREFM = 1), target pin: ANI0, ANI2 to ANI7, ANI16 to ANI24

(TA = -40 to +105°C, 2.4 V \leq VDD \leq 5.5 V, 2.4 V \leq EVDD0 \leq VDD, VSs = EVSs0 = 0 V, Reference voltage (+) = VBGR ^{Note 3}, Reference voltage (-) = AVREFM = 0 V ^{Note 4}, HS (high-speed main) mode)

Parameter	Symbol	Co	MIN.	TYP.	MAX.	Unit	
Resolution	RES				8		bit
Conversion time	tCONV	8-bit resolution	$2.4~V \leq V_{DD} \leq 5.5~V$	17		39	μs
Zero-scale error Notes 1, 2	Ezs	8-bit resolution	$2.4~V \leq V_{DD} \leq 5.5~V$			±0.60	% FSR
Integral linearity error Note 1	ILE	8-bit resolution	$2.4~V \le V_{DD} \le 5.5~V$			±2.0	LSB
Differential linearity error Note 1	DLE	8-bit resolution	$2.4~V \leq V_{DD} \leq 5.5~V$			±1.0	LSB
Analog input voltage	VAIN			0		VBGR Note 3	V

Note 1. Excludes quantization error (±1/2 LSB).

Note 2. This value is indicated as a ratio (% FSR) to the full-scale value.

Note 3. Refer to 3.6.2 Temperature sensor characteristics/internal reference voltage characteristic.

Note 4. When reference voltage (-) = Vss, the MAX. values are as follows.

Zero-scale error:Add ±0.35%FSR to the MAX. value when reference voltage (-) = AVREFM.Integral linearity error:Add ±0.5 LSB to the MAX. value when reference voltage (-) = AVREFM.Differential linearity error:Add ±0.2 LSB to the MAX. value when reference voltage (-) = AVREFM.



3.6.7 LVD circuit characteristics

(1) Reset Mode and Interrupt Mode

(TA = -40 to +105°C, VPDR \leq VDD \leq 5.5 V, VSS = 0 V)

Pa	Parameter		Conditions	MIN.	TYP.	MAX.	Unit
Voltage detection	Supply voltage level	VLVD0	Rising edge	3.90	4.06	4.22	V
threshold			Falling edge	3.83	3.98	4.13	V
		VLVD1	Rising edge	3.60	3.75	3.90	V
			Falling edge	3.53	3.67	3.81	V
		VLVD2	Rising edge	3.01	3.13	3.25	V
			Falling edge	2.94	3.06	3.18	V
		VLVD3	Rising edge	2.90	3.02	3.14	V
			Falling edge	2.85	2.96	3.07	V
		VLVD4	Rising edge	2.81	2.92	3.03	V
			Falling edge	2.75	2.86	2.97	V
		VLVD5	Rising edge	2.70	2.81	2.92	V
			Falling edge	2.64	2.75	2.86	V
		VLVD6	Rising edge	2.61	2.71	2.81	V
			Falling edge	2.55	2.65	2.75	V
		VLVD7	Rising edge	2.51	2.61	2.71	V
			Falling edge	2.45	2.55	2.65	V
Minimum pulse wid	lth	tLW		300			μs
Detection delay tim	le					300	μs



3.10 Timing of Entry to Flash Memory Programming Modes

<u>·</u>	•	1				
Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
How long from when an external reset ends until the initial communication settings are specified	tsuinit	POR and LVD reset must end before the external reset ends.			100	ms
How long from when the TOOL0 pin is placed at the low level until an external reset ends	tsu	POR and LVD reset must end before the external reset ends.	10			μs
How long the TOOL0 pin must be kept at the low level after an external reset ends (excluding the processing time of the firmware to control the flash memory)	thd	POR and LVD reset must end before the external reset ends.	1			ms





<1> The low level is input to the TOOL0 pin.

<2> The external reset ends (POR and LVD reset must end before the external reset ends).

<3> The TOOL0 pin is set to the high level.

<4> Setting of the flash memory programming mode by UART reception and complete the baud rate setting.

Remark tsuinit. The segment shows that it is necessary to finish specifying the initial communication settings within 100 ms from when the external resets end.

- tsu: How long from when the TOOL0 pin is placed at the low level until a pin reset ends
- tHD: How long to keep the TOOL0 pin at the low level from when the external resets end (excluding the processing time of the firmware to control the flash memory)

